Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

H558

APPLICATIONS

SWITCHING AND AMPLIFIER

ABSOLUTE MAXIMUM RATINGS (T_a=25℃)

T_{stg}——Storage Temperature····· -55~150℃

T_j——Junction Temperature·····150℃

P_C——Collector Dissipation·····500mW

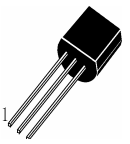
V_{CBO}——Collector-Base Voltage·····-30V

V_{CEO}——Collector-Emitter Voltage·····-30V

V_{EBO}——Emitter-Base Voltage·····-5V

I_C——Collector Current·····-100mA

TO-92



1—Collector，C
2—Base，B
3—Emitter，E

ELECTRICAL CHARACTERISTICS (T_a=25℃)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	-30			V	I_C=-100μA, I_E=0
BV_{CEO}	Collector-Emitter Breakdown Voltage	-30			V	I_C=-10mA, I_B=0
BV_{EBO}	Emitter-Base Breakdown Voltage	-5			V	I_E=-100μA，I_C=0
I_{CBO}	Collector Cut-off Current			-15	nA	V_{CB}=-30V, I_E=0
H_{FE}	DC Current Gain	110		800		V_{CE}=-5V, I_C=-2mA
$V_{CE(sat1)}$	Collector- Emitter Saturation Voltage		-90	-300	mV	I_C=-10mA, I_B=-0.5mA
$V_{CE(sat2)}$			-250	-650	mV	I_C=-100mA, I_B=-5mA
$V_{BE(sat1)}$	Base-Emitter Saturation Voltage		-0.7		V	I_C=-10mA, I_B=-0.5mA
$V_{BE(sat2)}$			-0.9		V	I_C=-100mA, I_B=-5mA
$V_{BE(ON1)}$	Base-Emitter On Voltage		-660	-750	mV	V_{CE}=-5V, I_C=-2mA
$V_{BE(ON2)}$				-800	mV	V_{CE}=-5V, I_C=-10mA
f_T	Current Gain-Bandwidth Product		150		MHz	V_{CE}=-5V, I_C=-10mA, f=1MHz
Cob	Output Capacitance			6	pF	V_{CB}=-10V, I_E=0，f=1MHz

h_{FE} Classification

A	B	C
110—220	200—450	420—800

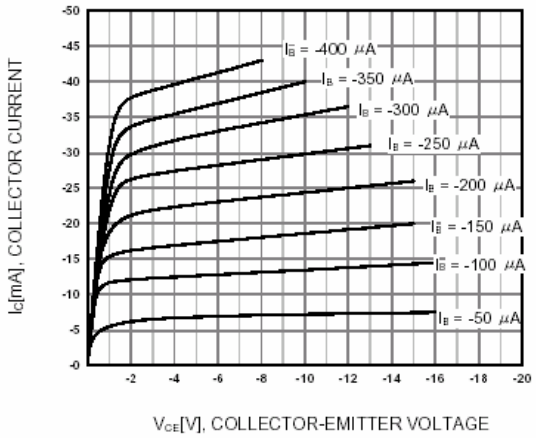


Figure 1. Static Characteristic

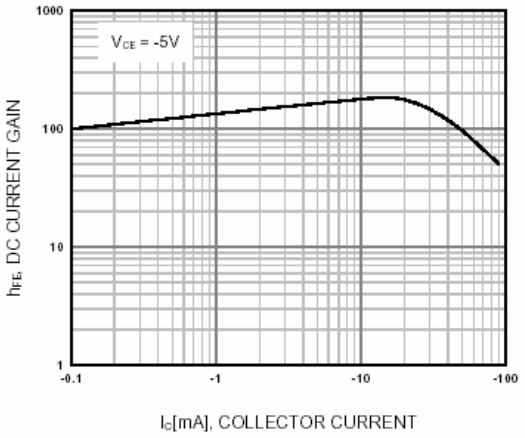


Figure 2. DC current Gain

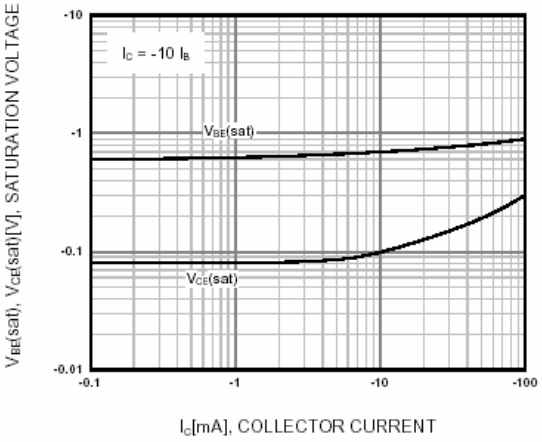


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

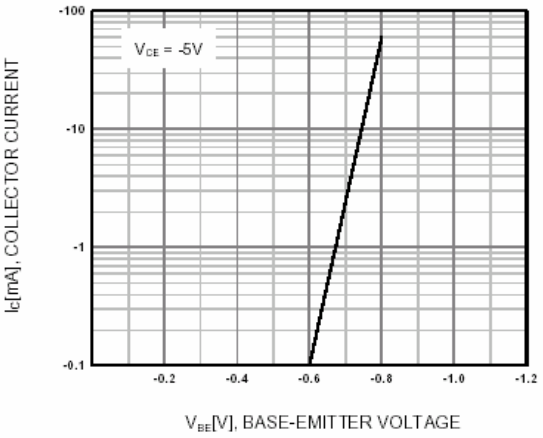


Figure 4. Base-Emitter On Voltage

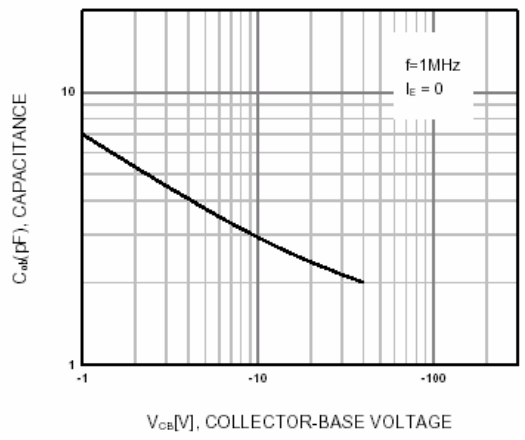


Figure 5. Collector Output Capacitance

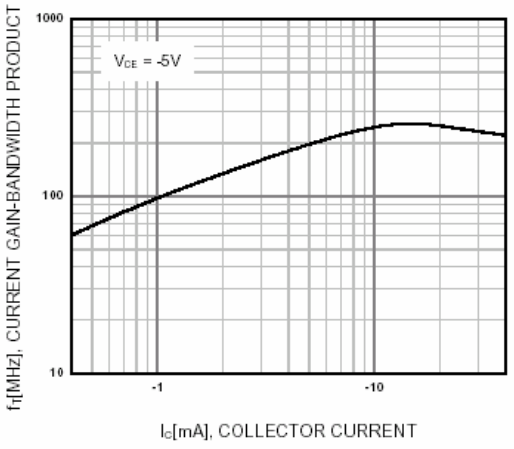


Figure 6. Current Gain Bandwidth Product